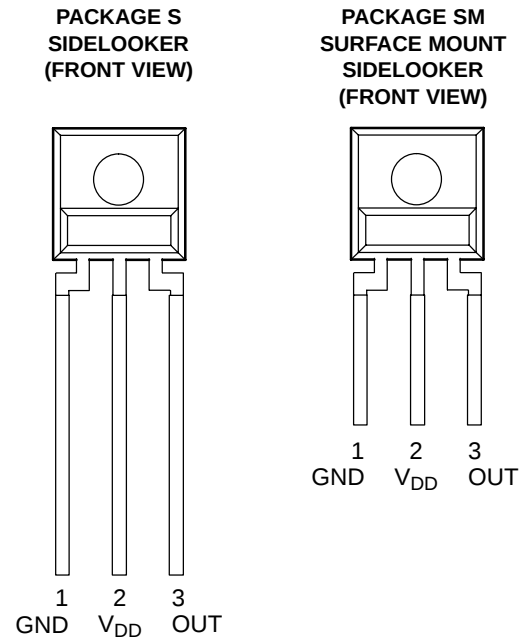


- High-Resolution Conversion of Light Intensity to Frequency With No External Components
- Communicates Directly With a Microcontroller
- Compact Three-Leaded Plastic Package
- Integral Visible-Light Cutoff Filter
- Single-Supply Operation . . . 2.7 V to 5.5 V
- High Irradiance Responsivity . . . Typically 500 Hz/($\mu\text{W}/\text{cm}^2$) at 940 nm
- Nonlinearity Error Typically 0.2% at 100 kHz
- Available in Through-Hole and Surface Mount Three-Lead Sidelooker Packages
- Replacement for TSL245
- Lead (Pb) Free Package Option Available



Description

The TSL245R light-to-frequency converter combines a silicon photodiode and a current-to-frequency converter on a single monolithic CMOS integrated circuit. Output is a square wave (50% duty cycle) with frequency directly proportional to light intensity (irradiance) on the photodiode. The digital output allows direct interface to a microcontroller or other logic circuitry. The TSL245R is characterized for operation over the temperature range of -25°C to 70°C and is supplied in a 3-lead plastic side-looker package with an integral visible-light cutoff filter and lens. When supplied in the lead (Pb) free package, the devices are RoHS compliant.

Functional Block Diagram



Available Options

DEVICE	T _A	PACKAGE – LEADS	PACKAGE DESIGNATOR	ORDERING NUMBER
TSL245R	-25°C to 70°	3-lead Sidelooker	S	TSL245R
TSL245R	-25°C to 70°	3-lead Sidelooker — Lead (Pb) Free	S	TSL245R-LF
TSL245R	-25°C to 70°	3-lead Surface Mount Sidelooker	SM	TSL245RSM
TSL245R	-25°C to 70°	3-lead Surface Mount Side-Looker — Lead (Pb) Free	SM	TSL245RSM-LF

TSL245R

INFRARED LIGHT-TO-FREQUENCY CONVERTER

TAOS060B – AUGUST 2005

Absolute Maximum Ratings over operating free-air temperature range (unless otherwise noted)[†]

Supply voltage, V_{DD} (see Note 1)	6 V
Operating free-air temperature range, T_A	–25°C to 70°C
Storage temperature range, T_{stg}	–25°C to 85°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds (S Package)	260°C
Reflow solder, 25 seconds maximum (SM Package)	260°C

[†] Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: All voltage values are with respect to GND.

Recommended Operating Conditions

	MIN	NOM	MAX	UNIT
Supply voltage, V_{DD}	2.7	5	5.5	V
Operating free-air temperature range, T_A	–25		70	°C

Electrical Characteristics at $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V_{OH} High-level output voltage	$I_{OH} = -4\text{ mA}$	4	4.5		V
V_{OL} Low-level output voltage	$I_{OL} = 4\text{ mA}$		0.25	0.4	V
I_{DD} Supply current			2	3	mA
Full-scale frequency [‡]		500			kHz
k_{SVS} Supply-voltage sensitivity	$V_{DD} = 5\text{ V} \pm 10\%$		± 0.5		%/V

[‡] Full-scale frequency is the maximum operating frequency of the device without saturation.

Operating Characteristics at $V_{DD} = 5\text{ V}$, $T_A = 25^\circ\text{C}$, $\lambda_p = 940\text{ nm}$

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
f_O Output frequency	$E_e = 40\text{ }\mu\text{W}/\text{cm}^2$	10	20	30	kHz
f_D Dark frequency	$E_e = 0\text{ }\mu\text{W}/\text{cm}^2$		0.4	10	Hz
R_e Irradiance responsivity			0.5		kHz/($\mu\text{W}/\text{cm}^2$)
Nonlinearity [§]	$f_O = 0\text{ kHz to }10\text{ kHz}$	$\pm 0.1\%$			%F.S.
	$f_O = 0\text{ kHz to }100\text{ kHz}$	$\pm 0.2\%$			%F.S.
Step response to full-scale step input		1 pulse of new frequency plus 1 μs			

[§] Nonlinearity is defined as the deviation of f_O from a straight line between zero and full scale, expressed as a percent of full scale.

TYPICAL CHARACTERISTICS

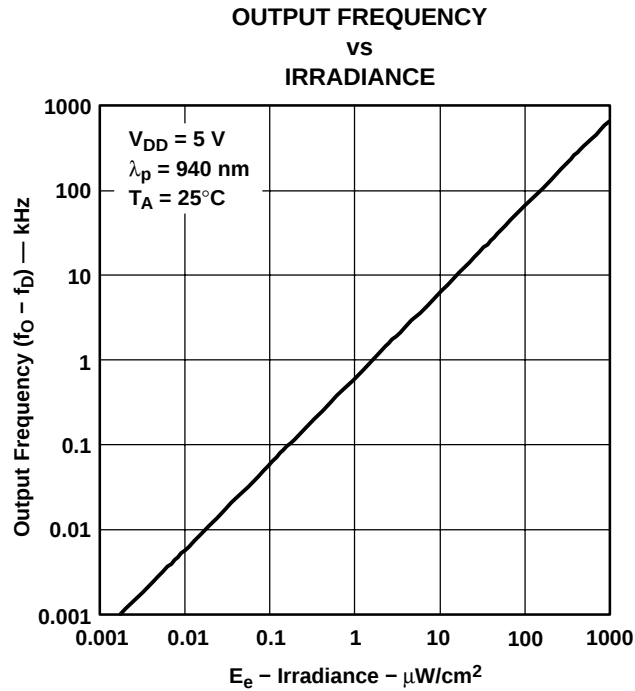


Figure 1

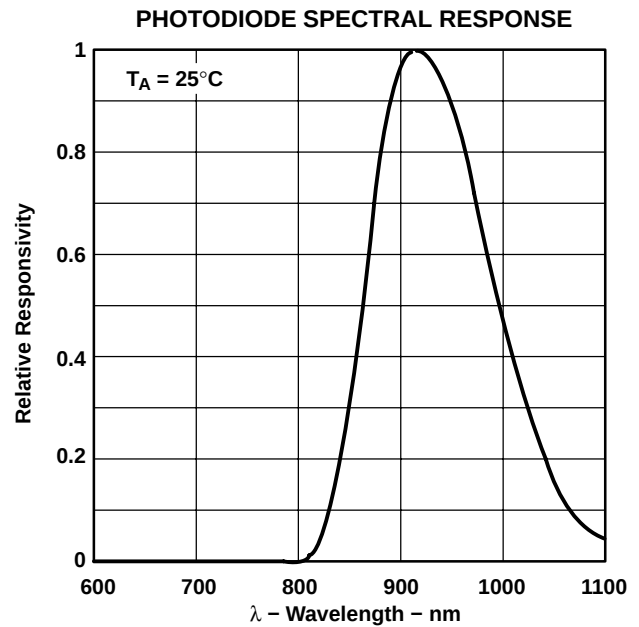


Figure 2

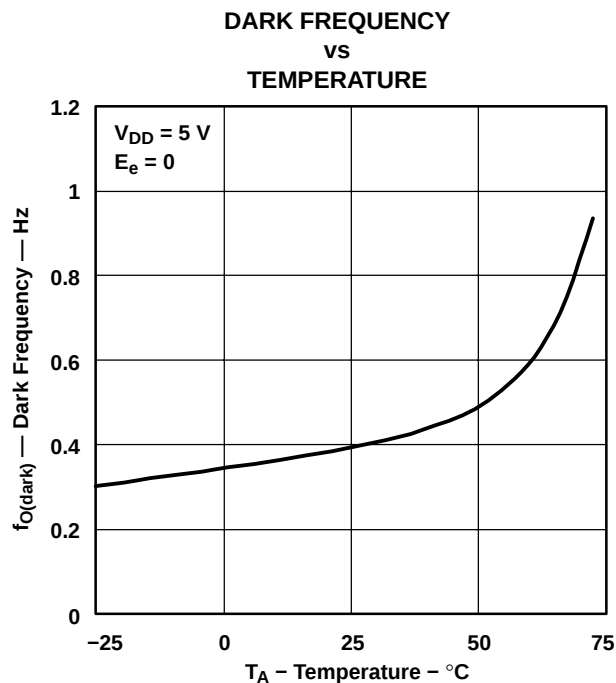


Figure 3

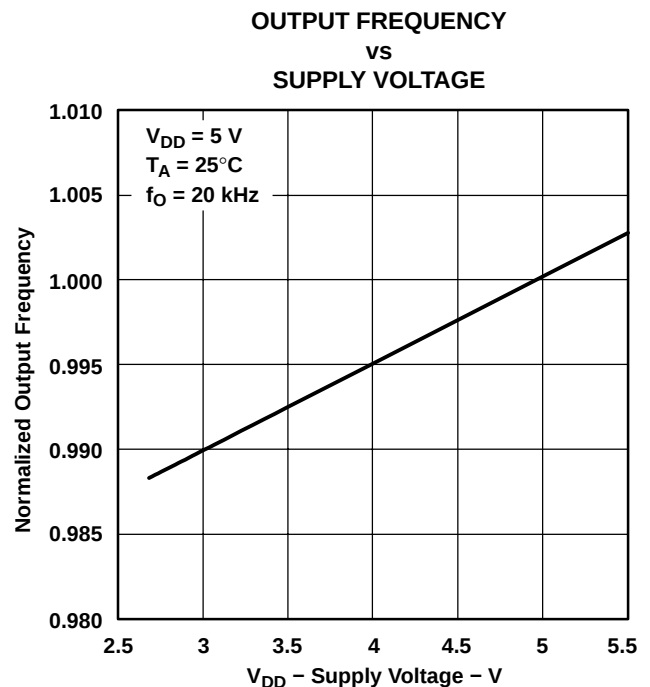


Figure 4

TSL245R INFRARED LIGHT-TO-FREQUENCY CONVERTER

TAOS060B – AUGUST 2005

APPLICATION INFORMATION

Power-supply considerations

Power-supply lines must be decoupled by a 0.01- μ F to 0.1- μ F capacitor with short leads placed close to the TSL245R (Figure 5). A low-noise power supply is required to minimize jitter on output pulse.

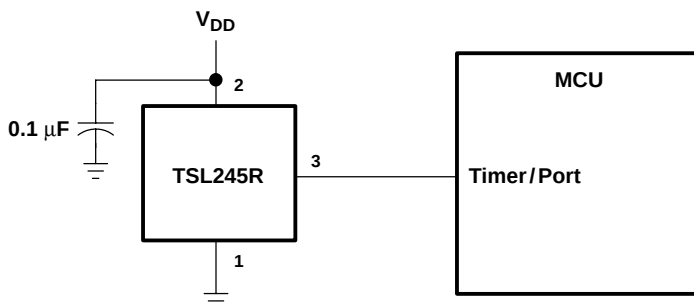


Figure 5. Typical TSL245R Interface to a Microcontroller

Device Operational Details

The frequency at the output pin (OUT) is given by:

$$f_O = f_D + (R_e)(E_e)$$

where:

- f_O is the output frequency
- f_D is the output frequency for dark condition ($E_e = 0$)
- R_e is the device responsivity for a given wavelength of light given in kHz/(μ W/cm²)
- E_e is the incident irradiance in μ W/cm²

f_D is an output frequency resulting from leakage currents. As shown in the equation above, this frequency represents a light-independent term in the total output frequency f_O . At very low light levels, this dark frequency can be a significant portion of f_O . The dark frequency is temperature dependent. For optimum performance of any given device over the full output range, the value of f_D should be measured (in the absence of light) and later subtracted from subsequent light measurement (see Figure 1).

Output interface

The output of the device is designed to drive a standard TTL or CMOS logic input over short distances. If lines greater than 12 inches are used on the output, a buffer or line driver is recommended.

Measuring the frequency

The choice of interface and measurement technique depends on the desired resolution and data-acquisition rate. For maximum data-acquisition rate, period-measurement techniques are used.

Period measurement requires the use of a fast reference clock with available resolution directly related to reference-clock rate. The technique is employed to measure rapidly varying light levels or to make a fast measurement of a constant light source.

Maximum resolution and accuracy may be obtained using frequency-measurement, pulse-accumulation, or integration techniques. Frequency measurements provide the added benefit of averaging out random- or high-frequency variations (jitter) resulting from noise in the light signal. Resolution is limited mainly by available counter registers and allowable measurement time. Frequency measurement is well suited for slowly varying or constant light levels and for reading average light levels over short periods of time. Integration, the accumulation of pulses over a very long period of time, can be used to measure exposure — the amount of light present in an area over a given time period.

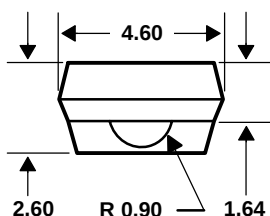


MECHANICAL DATA

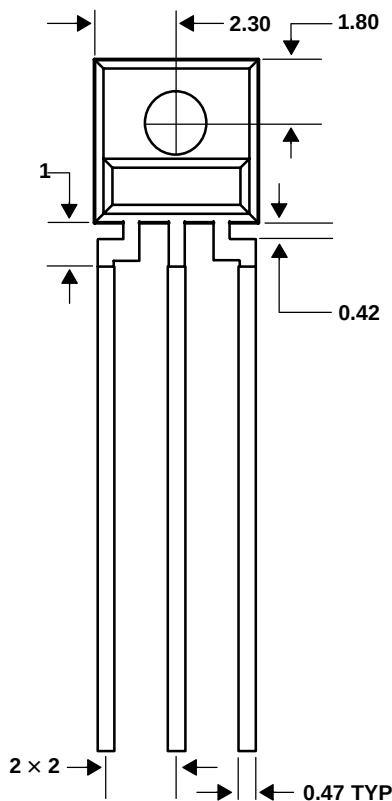
PACKAGE S

PLASTIC SINGLE-IN-LINE SIDE-LOOKER PACKAGE

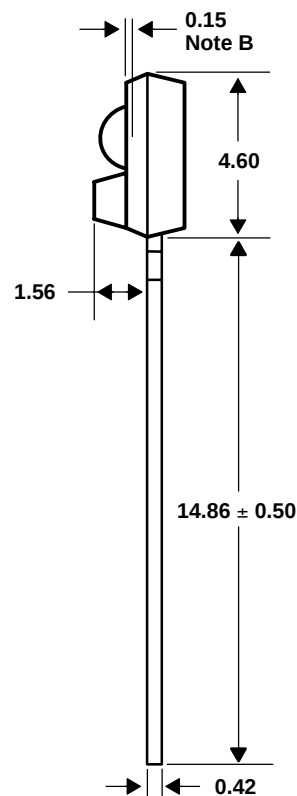
TOP VIEW



FRONT VIEW



SIDE VIEW



Lead Free
Available

- NOTES: A. All linear dimensions are in millimeters; tolerance is ± 0.25 mm unless otherwise stated.
 B. Dimension is to center of lens arc, which is located below the package face.
 C. The $0.96 \text{ mm} \times 0.96 \text{ mm}$ integrated photodiode active area is typically located in the center of the lens and 0.97 mm below the top of the lens surface.
 D. Lead finish for TSL245R: solder dipped, 63% Sn/37% Pb. Lead finish for TSL245xR-LF: solder dipped, 100% Sn.
 E. This drawing is subject to change without notice.

Figure 6. Package S — Single-In-Line Side-Looker Package Configuration

TSL245R INFRARED LIGHT-TO-FREQUENCY CONVERTER

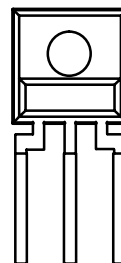
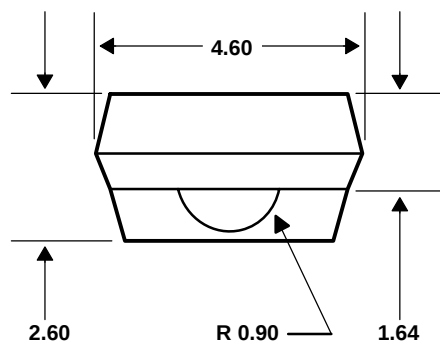
TAOS060B – AUGUST 2005

MECHANICAL DATA

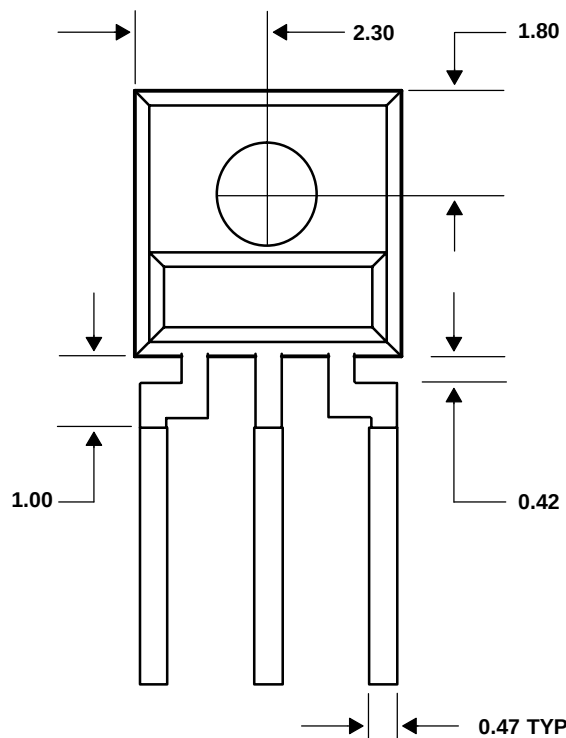
PACKAGE SM

PLASTIC SURFACE MOUNT SIDE-LOOKER PACKAGE

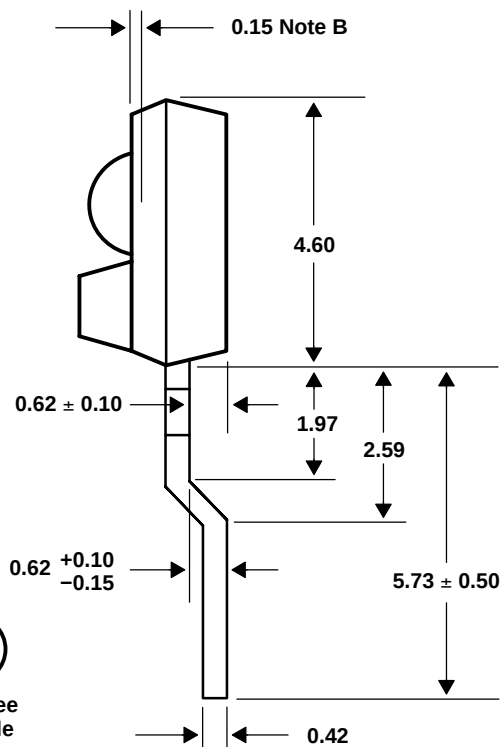
TOP VIEW



FRONT VIEW



SIDE VIEW



Lead Free
Available

- NOTES: A. All linear dimensions are in millimeters; tolerance is ± 0.25 mm unless otherwise stated.
 B. Dimension is to center of lens arc, which is located below the package face.
 C. The $0.96 \text{ mm} \times 0.96 \text{ mm}$ integrated photodiode active area is typically located in the center of the lens and 0.97 mm below the top of the lens surface.
 D. Lead finish for TSL245RSM: solder dipped, 63% Sn/37% Pb. Lead finish for TSL245xRSM-LF: solder dipped, 100% Sn.
 E. This drawing is subject to change without notice.

Figure 7. Package SM — Surface Mount Side-Looker Package Configuration



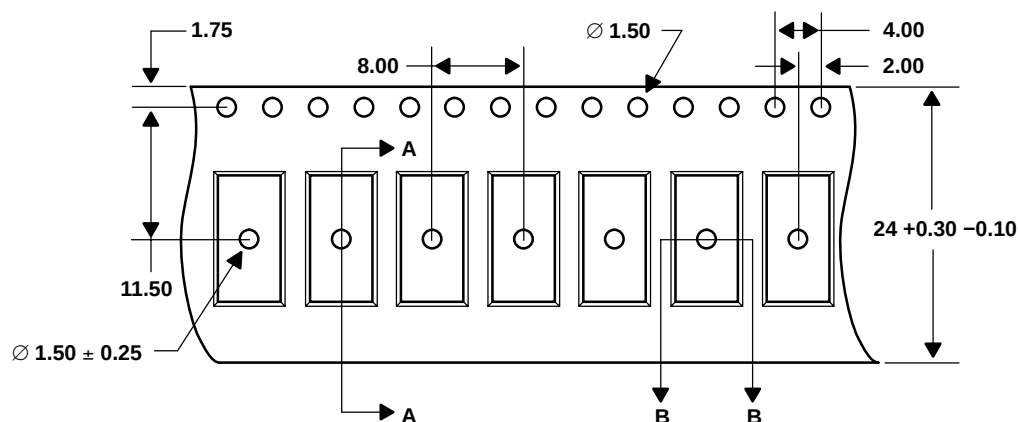
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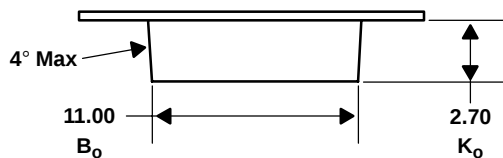
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MECHANICAL DATA

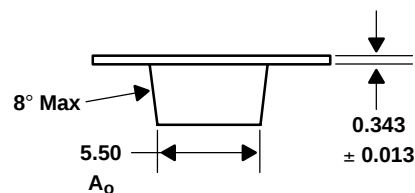
TOP VIEW



DETAIL A



DETAIL B



- NOTES:
- A. All linear dimensions are in millimeters, dimension tolerance is ± 0.10 mm unless otherwise noted.
 - B. The dimensions on this drawing are for illustrative purposes only. Dimensions of an actual carrier may vary slightly.
 - C. Symbols on drawing A_0 , B_0 , and K_0 are defined in ANSI EIA Standard 481-B 2001.
 - D. Each reel is 33 millimeters in diameter and contains 2500 parts.
 - E. TAOS packaging tape and reel conform to the requirements of EIA Standard 481-B.
 - F. Only surface mount parts (package SM) are supplied in tape and reel.
 - G. This drawing is subject to change without notice.

Figure 8. Package SM Carrier Tape

TSL245R

INFRARED LIGHT-TO-FREQUENCY CONVERTER

TAOS060B – AUGUST 2005

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